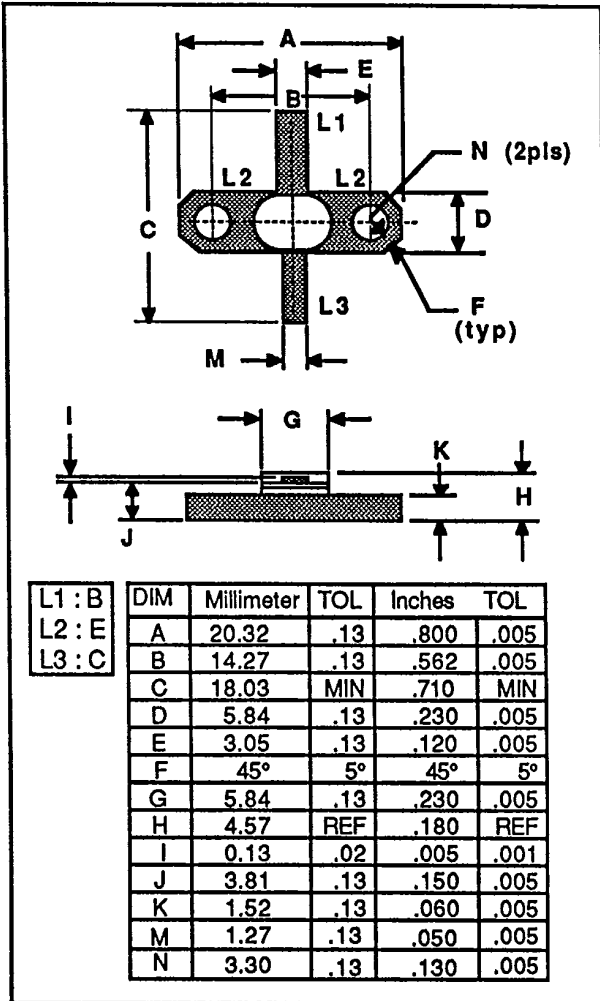


GENERAL DESCRIPTION

The 2003 is a common base transistor capable of providing 3 Watts of CW RF output power in the 1000-2000 MHz. This hermetically sealed transistor is specifically designed for Class C amplifier applications. It utilizes gold metallization and diffused ballasting to provide high reliability and supreme ruggedness.

2003
3 WATTS - 28 VOLTS
2000 MHz

MICROWAVE CW BIPOLAR



ABSOLUTE MAXIMUM RATINGS

Maximum Power Dissipation @ 25°C Case Temperature 11.6 W

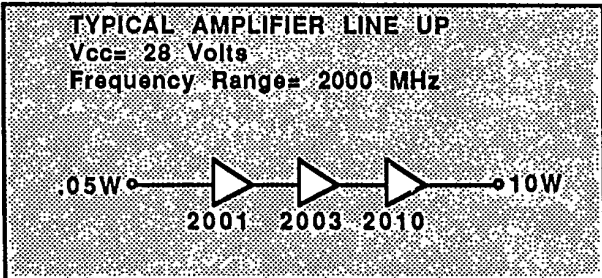
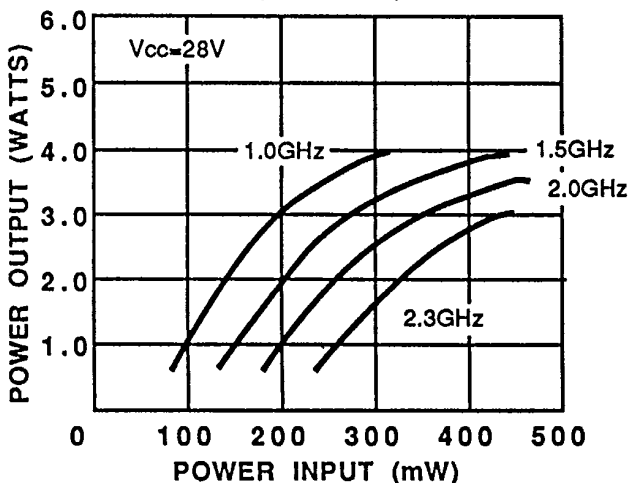
Maximum Voltage and Current

BVces Collector to Emitter Voltage 50 V
 BVebo Emitter to Base Voltage 3.5 V
 Ic Collector Current 0.5 A

Maximum Temperatures

Storage Temperature -65 to +200°C
 Operating Junction Temperature +200°C

POWER OUTPUT VS POWER INPUT (TYPICAL)



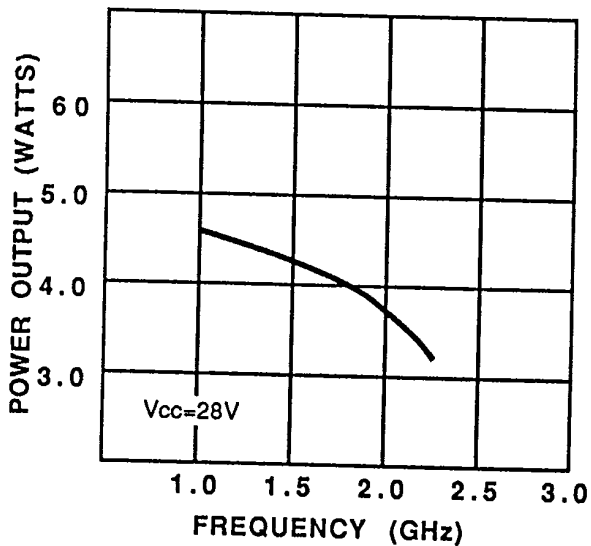
2003-2

ELECTRICAL CHARACTERISTICS¹

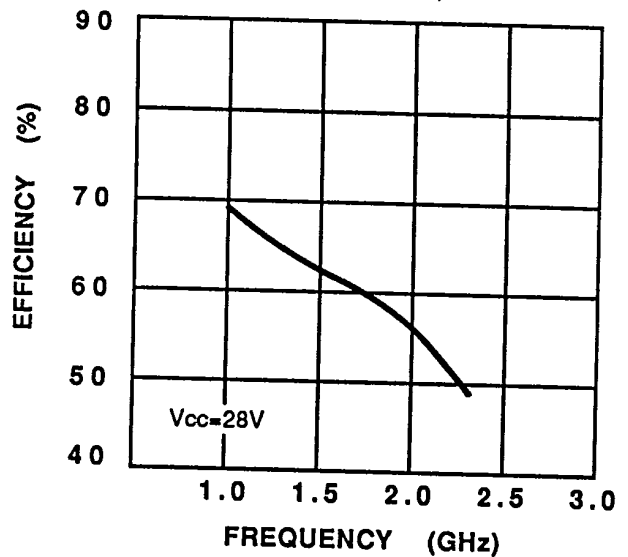
SYMBOL	CHARACTERISTICS	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
P _{out}	Power Output	f = 2000 MHz V _{cc} = 28V P _{in} = 0.47W	3.0			Watts
P _{in}	Power Input				0.47	Watts
P _g	Power Gain		8.1			dB
η _c	Collector Efficiency		40			%
VSWR	Load Mismatch Tolerance				∞:1	
B _{Vebo}	Breakdown Voltage (Emitter to Base)	I _c = 0A, I _e = 1.0mA	3.5			Volts
B _{Vces}	Breakdown Voltage (Collector to Emitter)	V _{be} = 0A, I _c = 10mA	50			Volts
B _{Vcbo}	Breakdown Voltage (Collector - Base)	I _e = 0A, I _c = 1mA	45			Volts
I _{cbo}	Collector Leakage Current	I _e = 0A, V _{cb} = 28V			500	μA
C _{ob}	Capacitance-Collector to Base	f = 1MHz, V _{cb} = 28V		5.0		pF
h _{FE}	DC-Current Gain	V _{ce} = 5V, I _c = 100mA	10			
θ _{jc}	Thermal Resistance	T _f = 25°C			15	°C/W

NOTE 1: T_c = 25°C unless otherwise specified.

POWER OUTPUT VS FREQUENCY (TYPICAL)



EFFICIENCY VS FREQUENCY (TYPICAL)

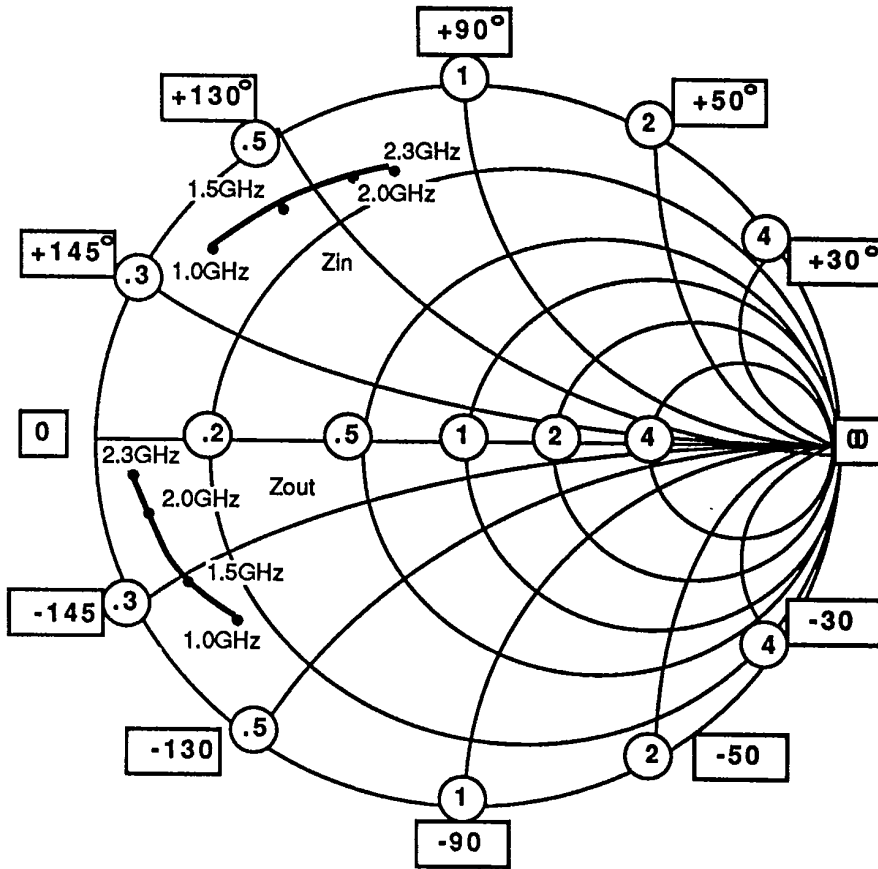


SPECIFICATIONS MAY BE SUBJECT TO CHANGE WITHOUT NOTICE

386

SMITH CHART 2003

NORMALIZED IMPEDANCE AND ADMITTANCE COORDINATES



NORMALIZED TO A 50 OHM SYSTEM.